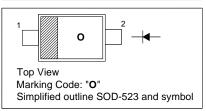
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25$ °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V _R	40	V
Average Forward Current	Io	100	mA
Maximum (Peak) Forward Current	I _{FM}	300	mA
Surge Current (10 ms)	I _{FSM}	1	А
Power Dissipation	P _{tot}	150	mW
Junction Temperature	T _J	125	°C
Operating Temperature Range	T _{opr}	- 40 to + 100	°C
Storage Temperature Range	T _s	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 50 mA	V _F	0.6	V
Reverse Current at V _R = 10 V	I _R	5	μΑ
Total Capacitance at f = 1 MHz	Ст	25	pF

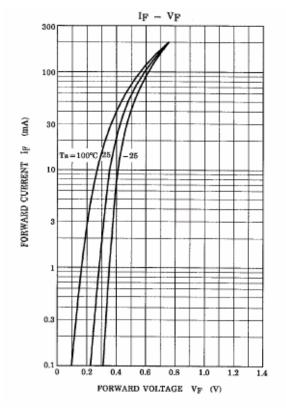


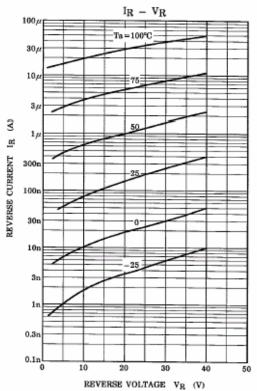


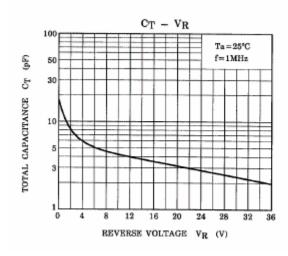


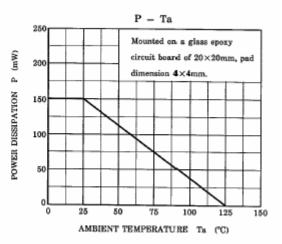


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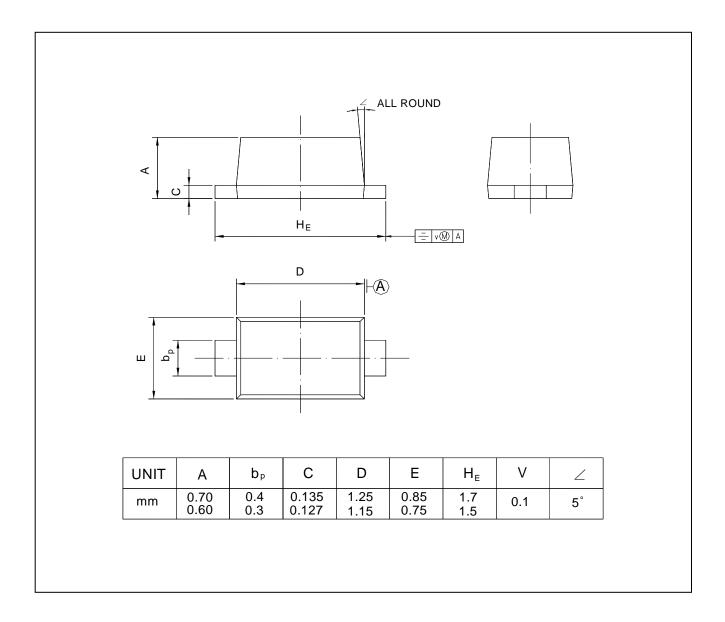




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523





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